

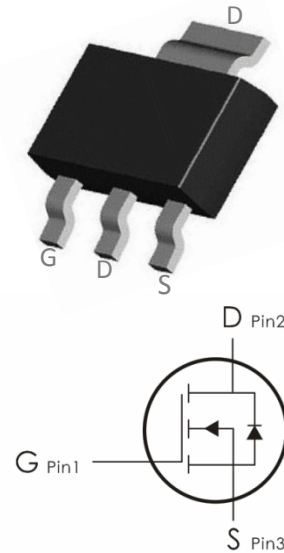
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=100V, I_D=8A, R_{DS(on)} < 90m\Omega @ V_{GS}=10V$ (Type : $75m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOT8N10	8N10	SOT- 223	4000 pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Curren ¹	8	A
	Continuous Drain Current- $T_A=70^\circ C$ ¹	4	
I_{DM}	Pulsed Drain Current ²	24	
P_D	Power Dissipation ⁴	2.5	W
E_{AS}	Single pulse avalanche energy ³	10.1	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to ambien	50	$^\circ C/W$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	100	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =80V	---	---	10	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1.2	---	2.9	V
R _{DS(ON)}	Drain-Source On Resistance ²	V _{GS} =10V, I _D =5A	---	75	90	m Ω
		V _{GS} =4.5V, I _D =3A	---	95	110	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	1008	---	pF
C _{OSS}	Output Capacitance		---	31	--	
C _{rss}	Reverse Transfer Capacitance		---	22	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =50V, I _D =5A, R _{ENG} =3 Ω ,V _{GS} =10V	---	37	---	ns
t _r	Rise Time		---	25.7	---	ns
t _{d(off)}	Turn-Off Delay Time		---	15	---	ns
t _f	Fall Time		---	8.7	---	ns
Q _{gs}	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =5A	---	16.3	---	nC
Q _{gd}	Gate-Source Charge		---	3.67	---	nC
Q _g	Gate-Drain “Miller” Charge		---	2.96	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _{SD} =1A	---	---	1.2	V
I _S	Continuous Drain Curren ^{1,5}	VD=VG=0V	---	---	8	A
I _{SM}	Pulsed Drain Current ^{2,5}		---	---	24	A

Notes:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=1mH, I_{AS}=4.5A$
- 4.The power dissipation is limited by 150 $^{\circ}\text{C}$ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

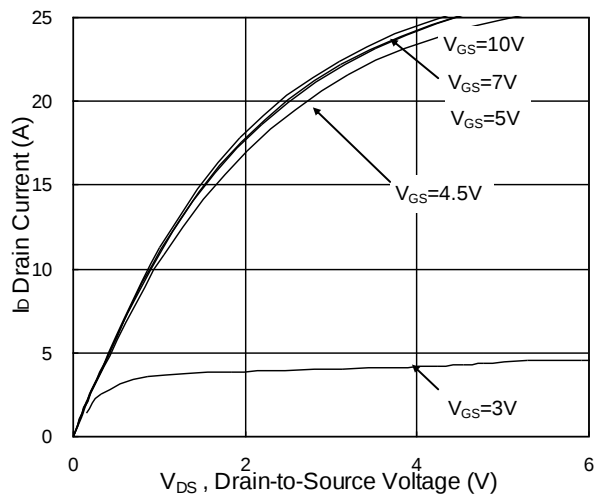


Fig.1 Typical Output Characteristics

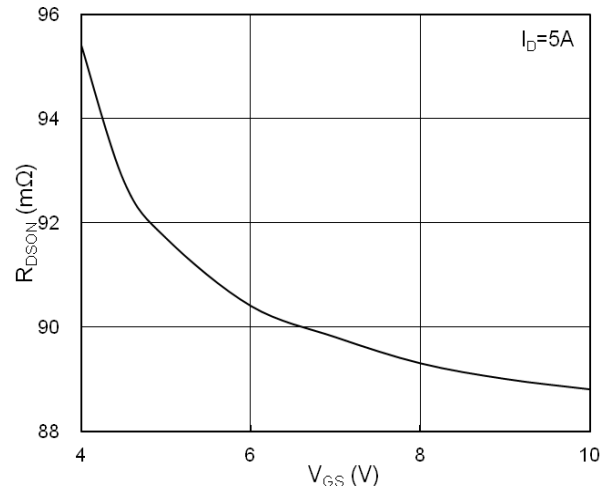


Fig.2 On-Resistance vs G-S Voltage

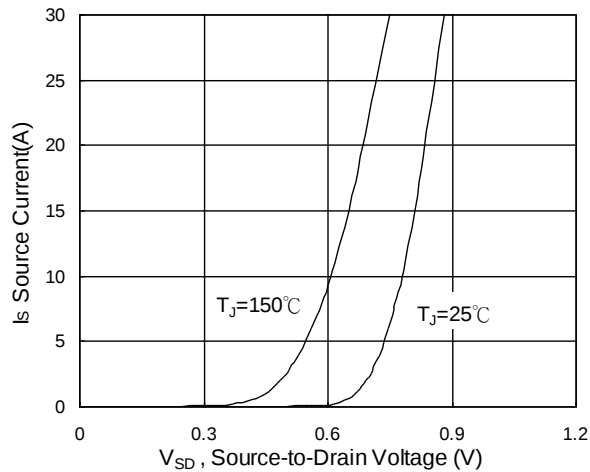


Fig.3 Source Drain Forward Characteristics

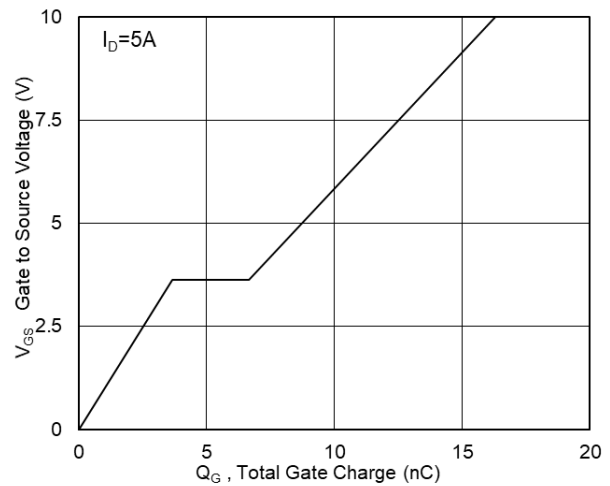


Fig.4 Gate-Charge Characteristics

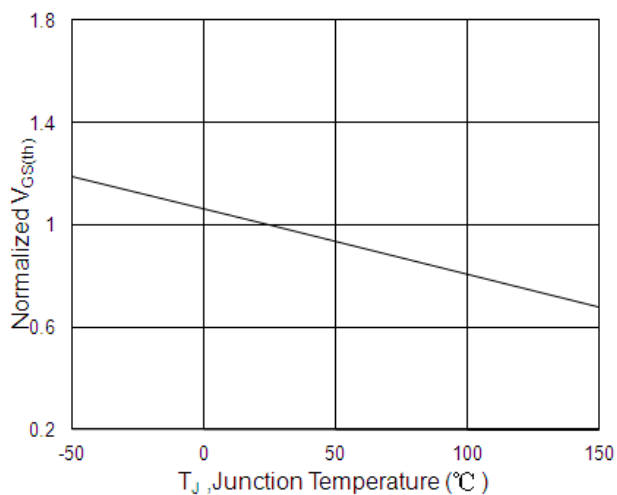


Fig.5 Normalized $V_{GS(th)}$ vs T_J

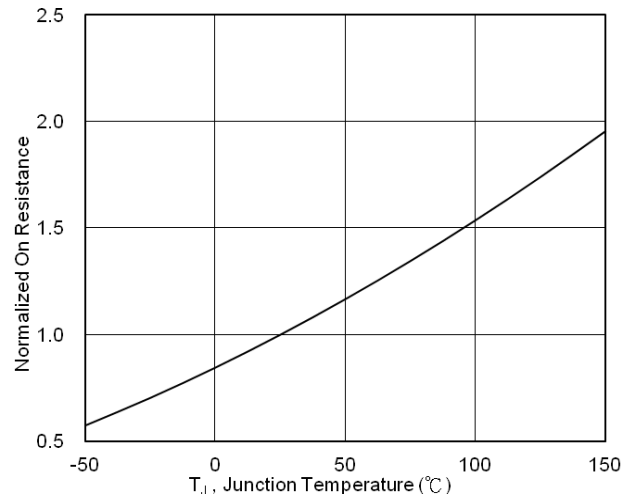


Fig.6 Normalized $R_{DS(on)}$ vs T_J

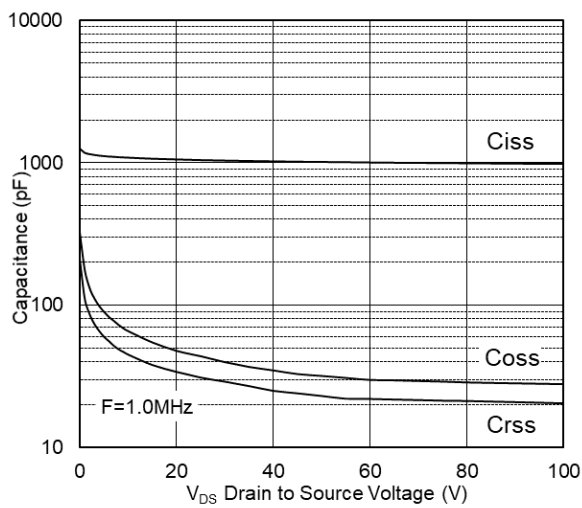


Fig.7 Capacitance

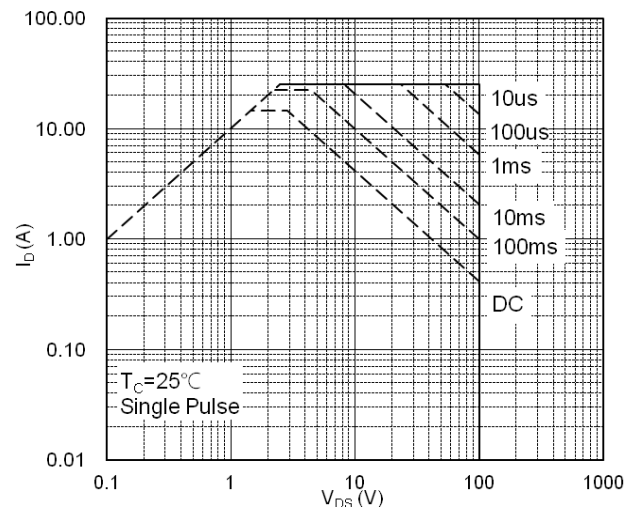


Fig.8 Safe Operating Area

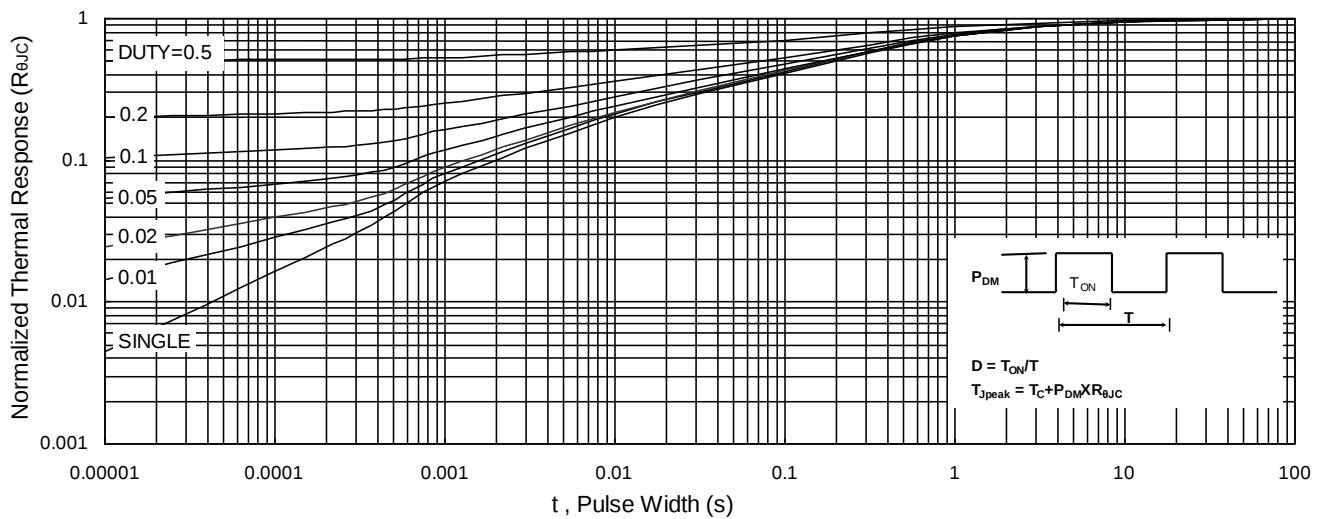
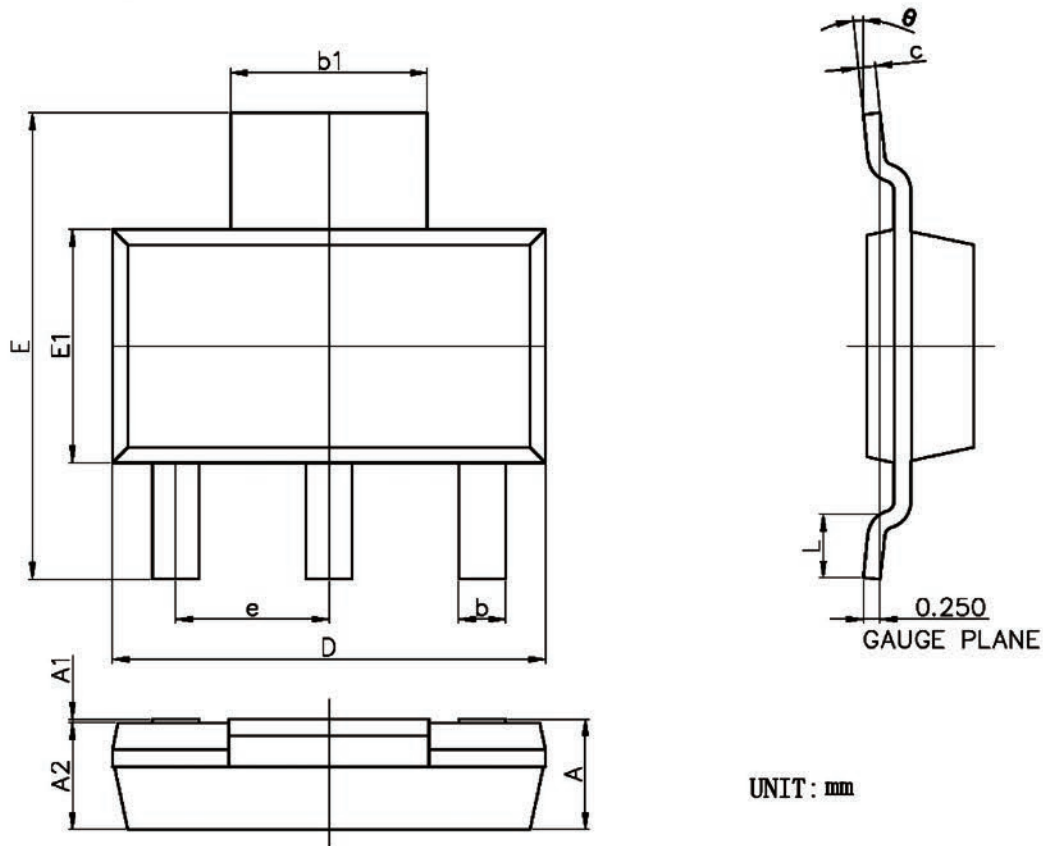


Fig.9 Normalized Maximum Transient Thermal Impedance

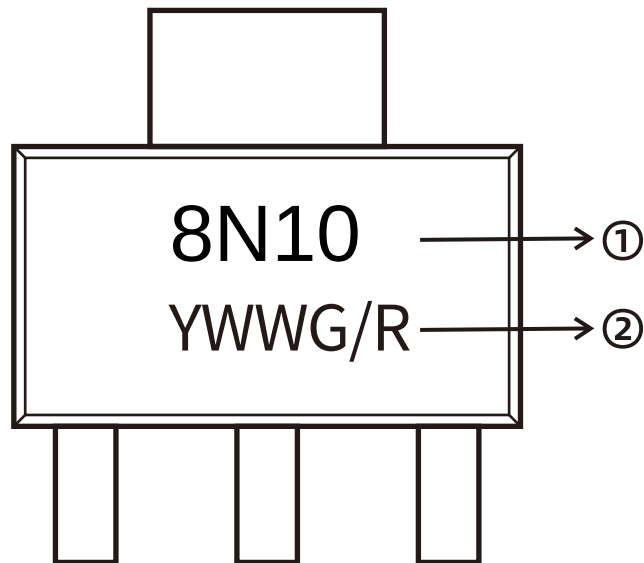
Sot-223 Package Outline Data


UNIT: mm

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	—	1.800	—	0.071
A1	0.020	0.100	0.001	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.840	0.026	0.033
b1	2.900	3.100	0.114	0.122
c	0.230	0.350	0.009	0.014
D	6.300	6.700	0.248	0.264
E	6.700	7.300	0.264	0.287
E1	3.300	3.700	0.130	0.146
e	2.300(BSC)		0.091(BSC)	
L	0.750	—	0.030	—
θ	0°	10°	0°	10°

Marking Information:

- ①: Part NO.
②: Date Code (YWWG / R)
Y: Year Code , last digit of the year
WW : Week Code (01-53)
G/R: G(Green) /R(Lead Free)



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